

Small-Signal Switching Diode

LL4148-G

Reverse Voltage: 100V

Forward Current: 150 mA



Features

Silicon Epitaxial Planar Diode

Fast switching diode in MiniMELF case especially suited for automatic insertion.

This diode is also available in other case styles including the standard 0603 case with the type designation CDSU4148, the standard 0805 case with the type designation CDSS4148 and the standard 1206 case with the type designation CDSN4148

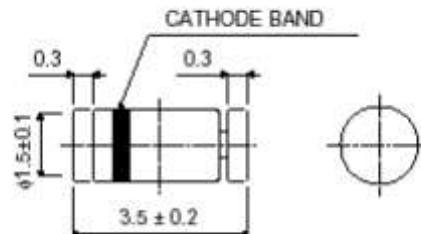
Mechanical Data

Case: MiniMELF Glass Case (SOD-80)

Weight: approx. 0.05g

Cathode Band Color: Black

MiniMELF (SOD-80)



Dimensions in mm

Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Reverse Voltage	V _R	75	V
Peak Reverse Voltage	V _{RM}	100	V
Forward DC Current at Tamb = 25°C ⁽¹⁾	I _F	200	mA
Average Rectified Current: Half Wave Rectification with Resistive Load at Tamb = 25°C f = 50 Hz ⁽¹⁾	I _{F(AV)}	150	mA
Surge Forward Current at t < 1s and Tj = 25°C	I _{FSM}	500	mA
Power Dissipation at Tamb = 25°C ⁽¹⁾	P _{tot}	500	mW
Thermal Resistance Junction to Ambient Air ⁽²⁾	R _{θJA}	350	°C/W
Thermal Resistance Junction to tie-point	R _{qJtp}	300	°C/W
Junction Temperature	T _j	175	°C
Storage Temperature	T _S	-65 to +175	°C

Electrical Characteristics (Tj = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V _F	I _F = 10mA	—	—	1	V
Leakage Current	I _R	VR = 20V	—	—	25	nA
		VR = 75V	—	—	5	μA
		VR = 20V, TJ = 150°C	—	—	50	μA
		C _{tot}	V _F = VR = 0	—	4	pF
Voltage Rise when Switching ON (tested with 50 mA forward Pulses)	V _f	tp = 0.1μs, Rise time < 30ns fp = 5 to 100kHz	—	—	2.5	V
Reverse Recovery Time	trr	I _F = 10mA, I _R = 1mA, VR = 6V, RL = 100Ω	—	—	4	ns
Rectification Efficiency (See third page)	η _V	f = 100MHz, V _{RF} = 2V	0.45	—	—	—

Notes: (1) Valid provided that electrodes are kept at ambient temperature

(2) Device mounted on FR4 printed-circuit board

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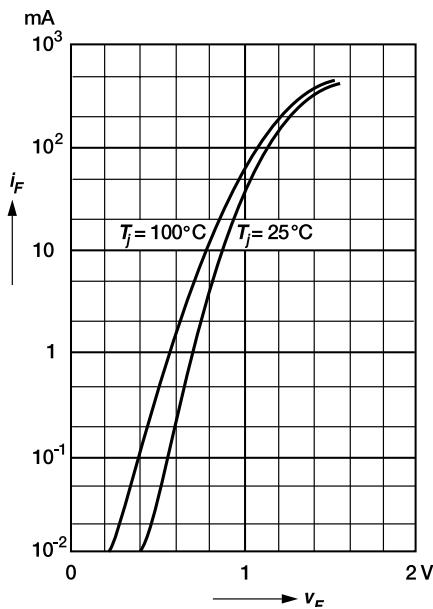
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SMD DIODE SPECIALIST

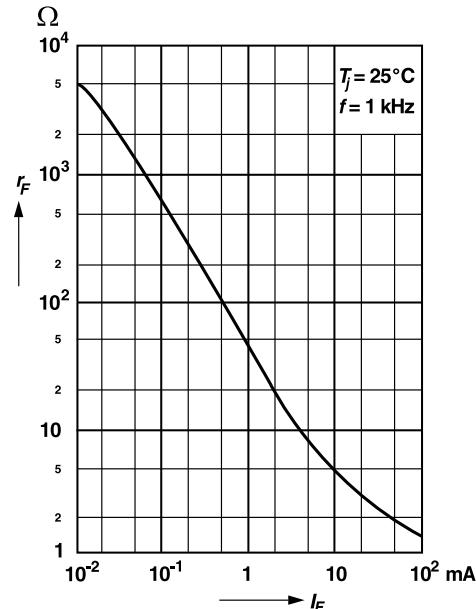


Ratings and Characteristic Curves(TA = 25°C unless otherwise noted)

Forward characteristics

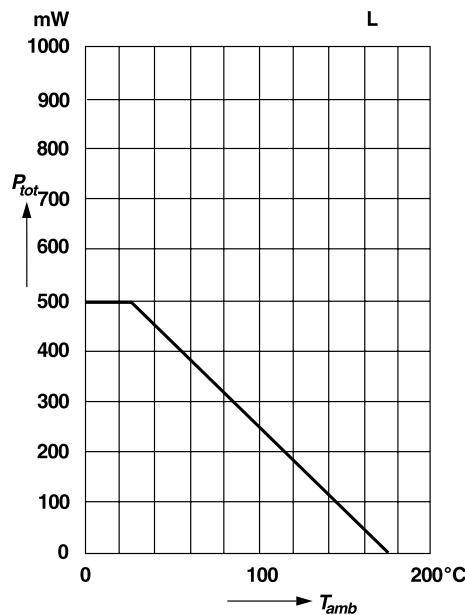


Dynamic forward resistance
versus forward current

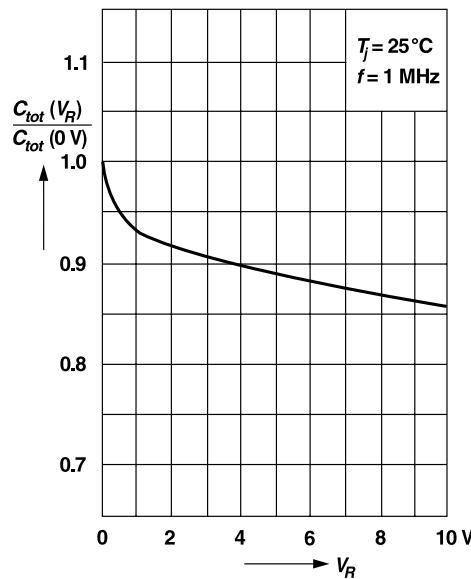


Admissible power dissipation
versus ambient temperature

Valid provided that electrodes are kept at ambient temperature



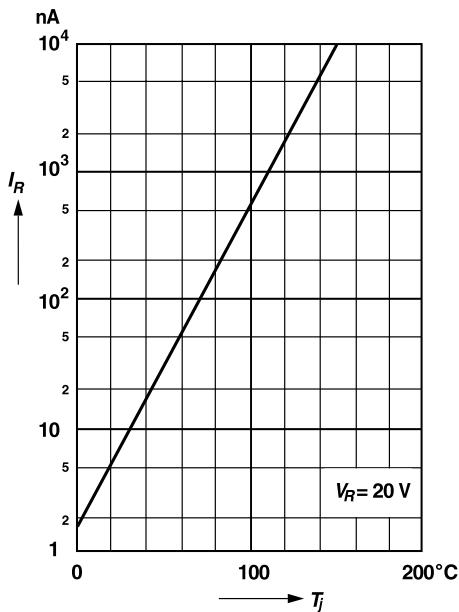
Relative capacitance
versus reverse voltage



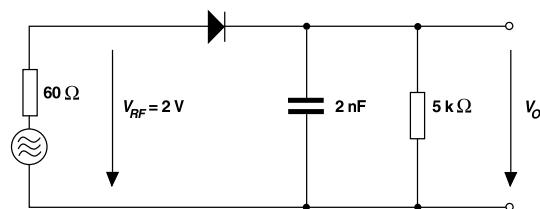


Ratings and Characteristic Curves(TA = 25°C unless otherwise noted)

Leakage current
versus junction temperature



Rectification Efficiency Measurement Circuit



Admissible repetitive peak forward current versus pulse duration

Valid provided that electrodes are kept at ambient temperature

